

ROHS

HALOGEN

FREE

Ultrafast Rectifier, 2 A FRED Pt®



MicroSMP (DO-219AD)

Anode O Cathode

DESIGN SUPPORT TOOLS AVAILABLE



PRIMARY CHARACTERISTICS					
I _{F(AV)}	2 A				
V_{R}	100 V, 200 V				
V _F at I _F	0.82 V				
t _{rr} (typ.)	33 ns				
I _{FSM}	30 A				
T _J max.	175 °C				
Package	MicroSMP (DO-219AD)				
Circuit configuration	Single				

FEATURES

- Very low profile typical height of 1.0 mm
- · Ideal for automated placement
- · Low forward voltage drop, low power losses
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- For PFC, CRM snubber operation
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATION

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial and automotive applications.

MECHANICAL DATA

Case: MicroSMP (DO-219AD)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 33-N102

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse	VS-2EQH01-M3	V		100	V
voltage VS-2EQH02-M3	VS-2EQH02-M3	V_{RRM}		200	
Average rectified forward current		I _{F(AV)}	T _M = 137 °C	2	Α
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C, 10 ms sine pulse	30	A
Operating junction and st	orage temperatures	T _J , T _{Stg}		-55 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage,	VS-2EQH01-M3	V _{BR} ,	L = 100 uA	100	-	-	
blocking voltage	VS-2EQH02-M3	V_R	$I_{R} = 100 \mu A$	200			V
Forward voltage	,		I _F = 2 A	-	0.96	1.05	V
Forward voltage		V _F	I _F = 2 A, T _J = 150 °C	-	0.82	0.84	
Reverse leakage current		1	V _R = V _R rated	-	-	1	
		I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	-	25	μΑ
Junction capacitance		C _T	V _R = 200 V	-	6	-	pF



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt = 5$	$0 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	-	33	-	
Reverse recovery time t	+	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	i	23	
	t _{rr}	T _J = 25 °C		-	19	-	ns A
		T _J = 125 °C	$I_F = 2 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 100 \text{ V}$	-	33	-	
Peak recovery current	1	T _J = 25 °C		-	1.7	-	
	I _{RRM}	T _J = 125 °C		-	2.5	-	
Reverse recovery charge	0	T _J = 25 °C		-	15	=	nC
	Q _{rr}	T _J = 125 °C		-	34	-	IIC

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction at temperature range	nd storage	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, j	junction to mount	R _{thJM} ⁽¹⁾		-	16	20	
Thermal resistance, j	junction to ambient	R _{thJA}	Device mounted on FR4 PCB, 2 oz. standard footprint	-	160	-	°C/W
Marking dayioo	VS-1EQH01-M3		Case style MicroSMP (DO-219AD)	2H1			
Marking device	VS-2EQH02-M3		Case style iviiciosivir (DO-219AD)		2H2		

Note

⁽¹⁾ Thermal resistance junction to mount follows JEDEC® 51-14 transient dual interface test method (TDIM)

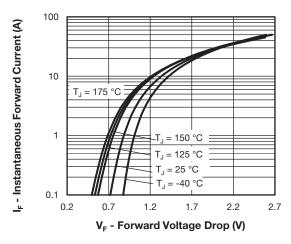


Fig. 1 - Typical Forward Voltage Drop Characteristics

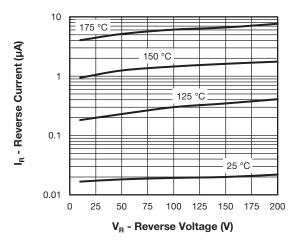


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

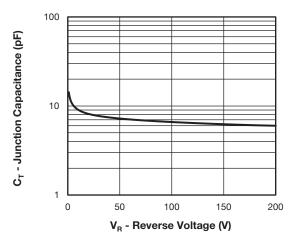


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

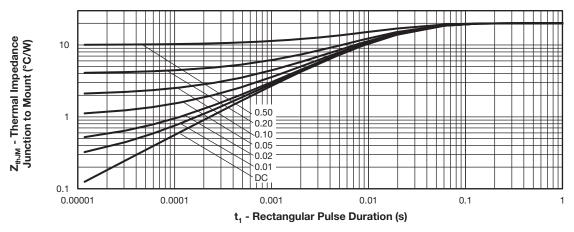


Fig. 4 - Maximum Transient Thermal Impedance, Junction to Mount

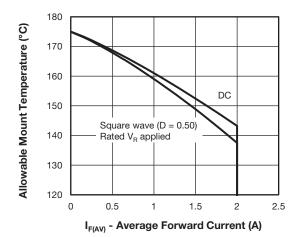


Fig. 5 - Maximum Allowable Mount Temperature vs. Average Forward Current

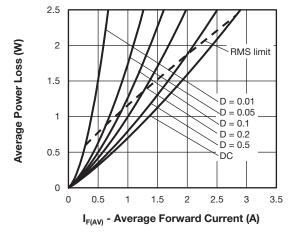


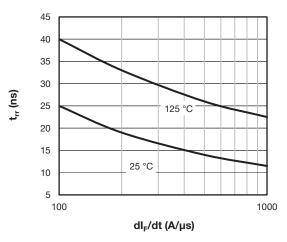
Fig. 6 - Forward Power Loss Characteristics

Note

Formula used: $T_M = T_J - (Pd + Pd_{REV}) \times R_{thJM}$; $Pd = forward power loss = I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 5); $Pd_{REV} = inverse$ power loss = $V_{R1} \times I_R$ (1 - D); I_R at $V_{R1} = rated V_R$

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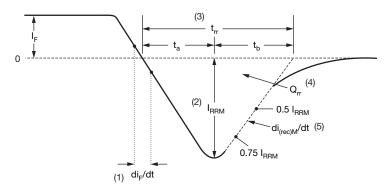


45 40 35 30 35 25 20 15 100 1000 dl_F/dt (A/µs)

50

Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_F$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

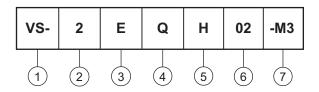
(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Current rating (2 = 2 A)

3 - Circuit configuration:

E = single diode

4 - Q = MicroSMP package

5 - Process type,

H = ultrafast recovery

Voltage code (02 = 200 V)

- -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

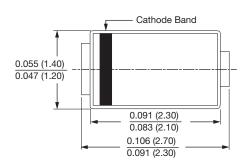
ORDERING INFORMATION (Example)						
PREFERRED P/N	PREFERRED PACKAGE CODE MINIMUM ORDER QUANTITY PACKAGING DESCRIP					
VS-2EQH01-M3/H	Н	4500	7" diameter plastic tape and reel			
VS-2EQH02-M3/H	Н	4500	7" diameter plastic tape and reel			

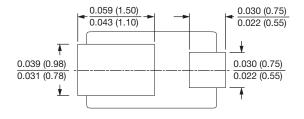
LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96591</u>				
Part marking information	www.vishay.com/doc?96590			
Packaging information	www.vishay.com/doc?88869			
SPICE model	www.vishay.com/doc?96595			

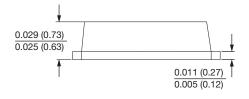


MicroSMP (DO-219AD), FRED Pt®

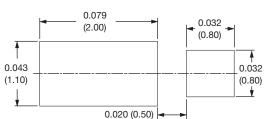
DIMENSIONS in inches (millimeters)







Mounting Pad Layout





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Vishay

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